

MOSFET - Power, Single N-Channel STD Gate, SO8FL

80 V, 3 mΩ, 135 A
NVMFWS3D0N08X

Features

- Low Q_{RR} , Soft Recovery Body Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Synchronous Rectification (SR) in DC-DC and AC-DC
- Primary Switch in Isolated DC-DC Converter
- Motor Drives
- Automotive 48 V System

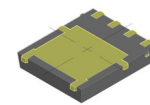
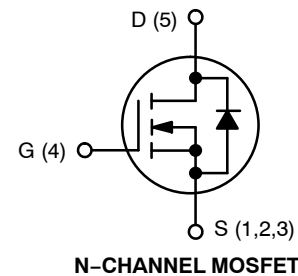
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	80	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Power Dissipation (Note 1)	P_D	119	W
Pulsed Drain Current	I_{DM}	543	A
Pulsed Source Current (Body Diode)	I_{SM}	543	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	179	A
Single Pulse Avalanche Energy ($I_{PK} = 47\text{ A}$) (Note 2)	E_{AS}	110	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

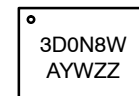
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Actual continuous current will be limited by thermal & electromechanical application board design.
3. E_{AS} of 110 mJ is based on started $T_J = 25^\circ\text{C}$, $I_{AS} = 55\text{ A}$, $V_{DD} = 64\text{ V}$, $V_{GS} = 10\text{ V}$, 100% avalanche tested.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	3 mΩ @ 10 V	135 A



DFNW5 (SO-8FL)
CASE 507BA



3D0N8W = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 3 of this data sheet.

NVMFWS3D0N08X

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.26	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	39	

4. Surface-mounted on FR4 board using 1 in² pad size, 1 oz. Cu pad.

5. $R_{\theta JA}$ is determined by the user's board design.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
-----------	--------	-----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}$, Referenced to 25°C		31.6		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{ V}, T_J = 25^\circ\text{C}$			1	μA
		$V_{DS} = 80\text{ V}, T_J = 125^\circ\text{C}$			250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 31\text{ A}$		2.6	3.0	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 153\text{ μA}$	2.4		3.6	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 153\text{ μA}$		-7.5		mV/°C
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 31\text{ A}$		97		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$		2680		pF
Output Capacitance	C_{OSS}			780		
Reverse Transfer Capacitance	C_{RSS}			12		
Output Charge	Q_{OSS}			56		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 6\text{ V}, V_{DD} = 40\text{ V}, I_D = 31\text{ A}$		23		nC
		$V_{GS} = 10\text{ V}, V_{DD} = 40\text{ V}, I_D = 31\text{ A}$		38		
Threshold Gate Charge	$Q_{G(TH)}$			7		
Gate-to-Source Charge	Q_{GS}			13		
Gate-to-Drain Charge	Q_{GD}			6		
Gate Plateau Voltage	V_{GP}			4.7		V
Gate Resistance	R_G	$f = 1\text{ MHz}$		0.7		Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 0/10\text{ V}, V_{DD} = 64\text{ V},$ $I_D = 31\text{ A}, R_G = 2.5\text{ Ω}$		22		ns
Rise Time	t_r			8		
Turn-Off Delay Time	$t_{d(OFF)}$			33		
Fall Time	t_f			5		

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 31\text{ A}, T_J = 25^\circ\text{C}$		0.82	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 31\text{ A}, T_J = 125^\circ\text{C}$		0.66		

NVMFWS3D0N08X

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
-----------	--------	-----------------	-----	-----	-----	------

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI/dt = 1000 A/μs, I _S = 31 A, V _{DD} = 64 V		22		ns
Charge Time	t _a			13		
Discharge Time	t _b			9		
Reverse Recovery Charge	Q _{RR}			150		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFWS3D0N08XT1G	3D0N8W	DFNW5 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

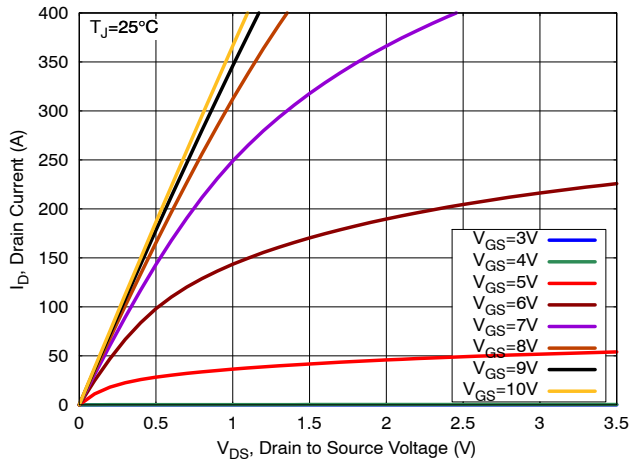


Figure 1. On-Region Characteristics

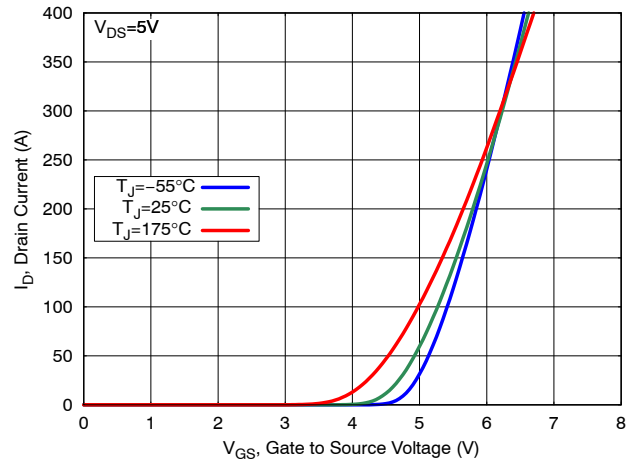


Figure 2. Transfer Characteristics

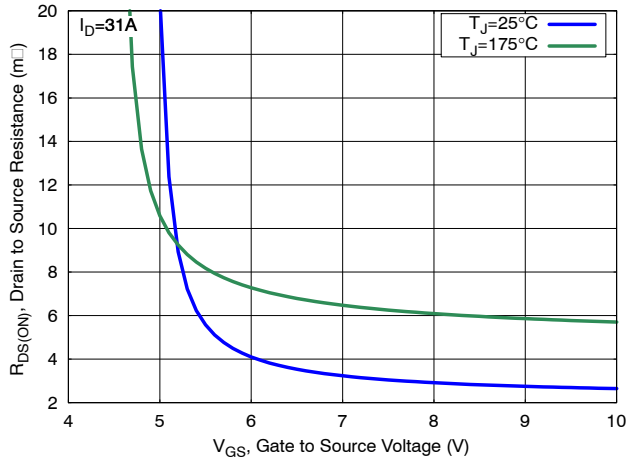


Figure 3. On-Resistance vs. Gate Voltage

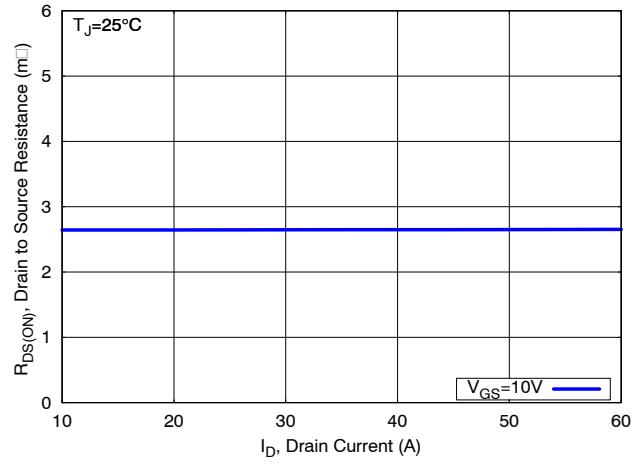


Figure 4. On-Resistance vs. Drain Current

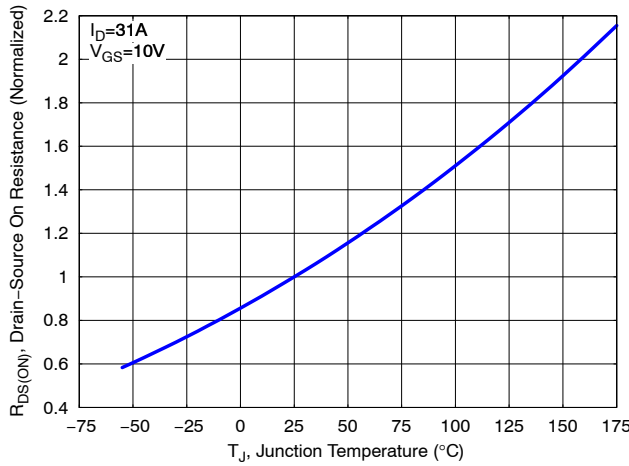


Figure 5. Normalized ON Resistance vs. Junction Temperature

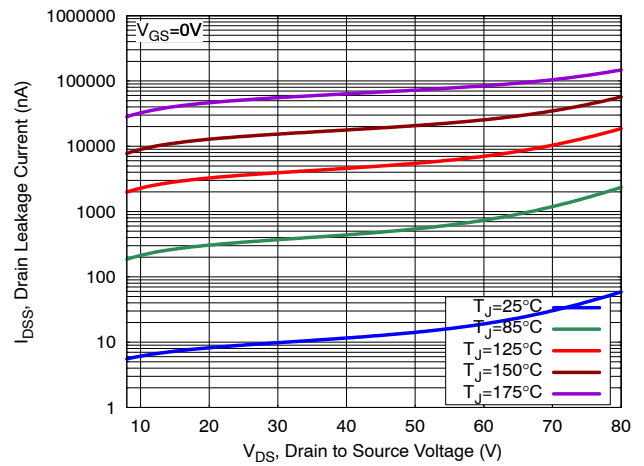


Figure 6. Drain Leakage Current vs. Drain Voltage

NVMFWS3D0N08X

TYPICAL CHARACTERISTICS

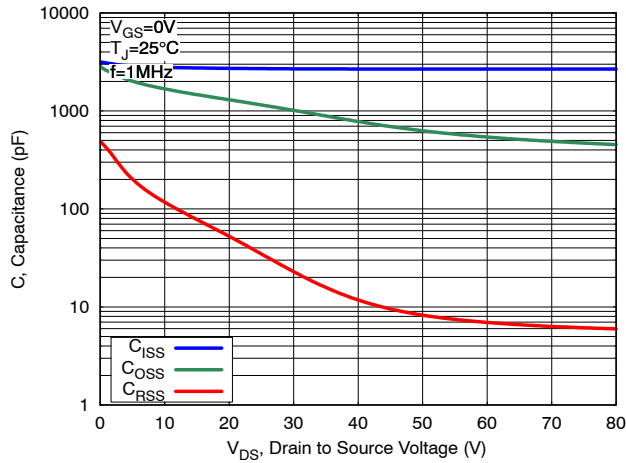


Figure 7. Capacitance Characteristics

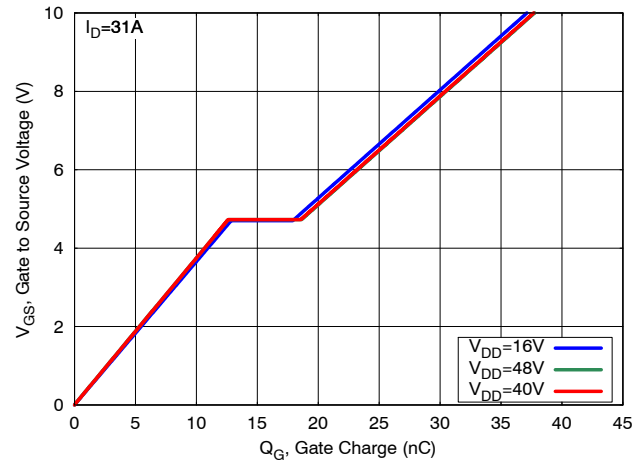


Figure 8. Gate Charge Characteristics

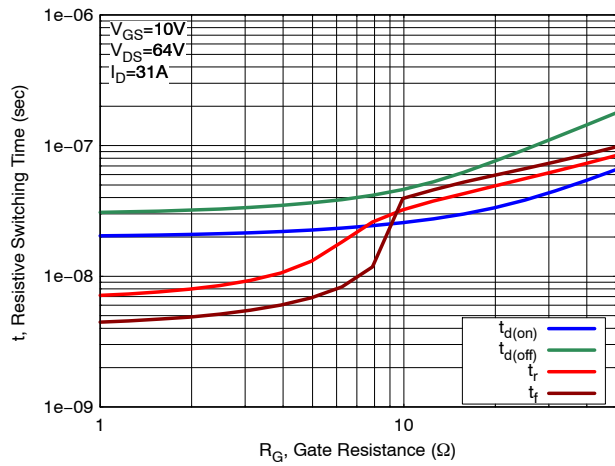


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

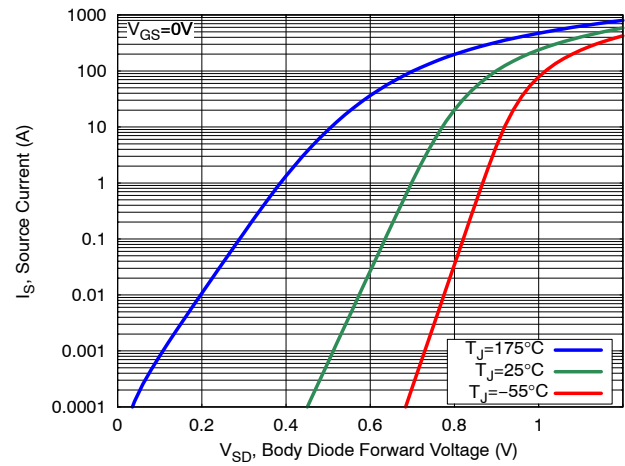


Figure 10. Diode Forward Characteristics

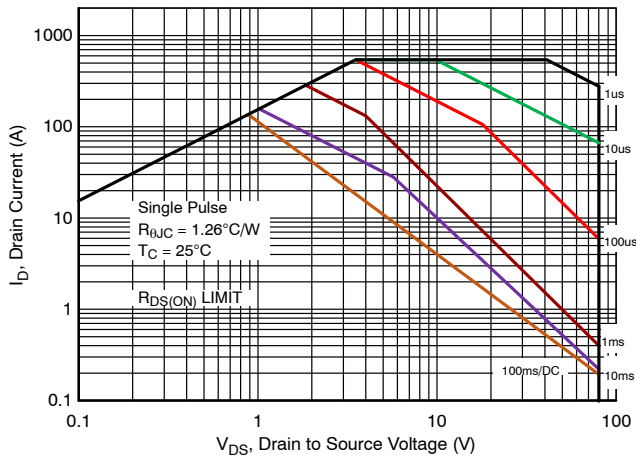


Figure 11. Safe Operating Area (SOA)

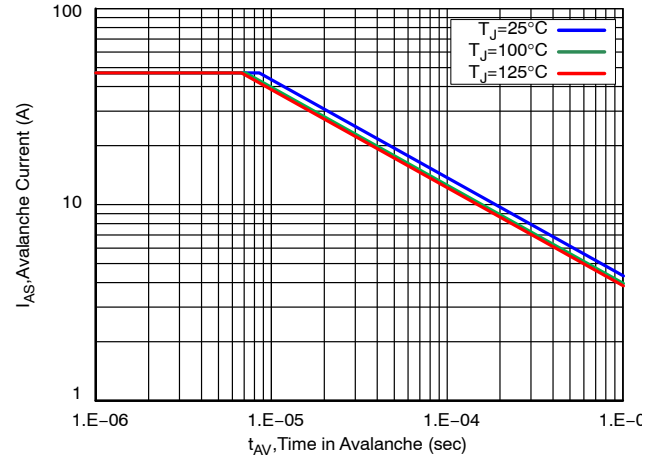


Figure 12. Avalanche Current vs Pulse Time (UIS)

NVMFWS3D0N08X

TYPICAL CHARACTERISTICS

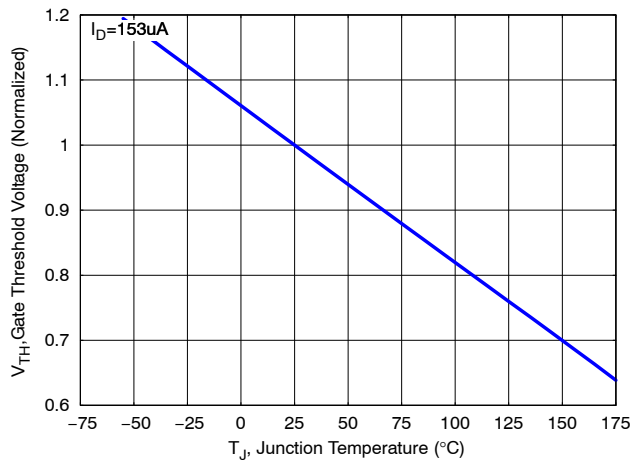


Figure 13. Gate Threshold Voltage vs Junction Temperature

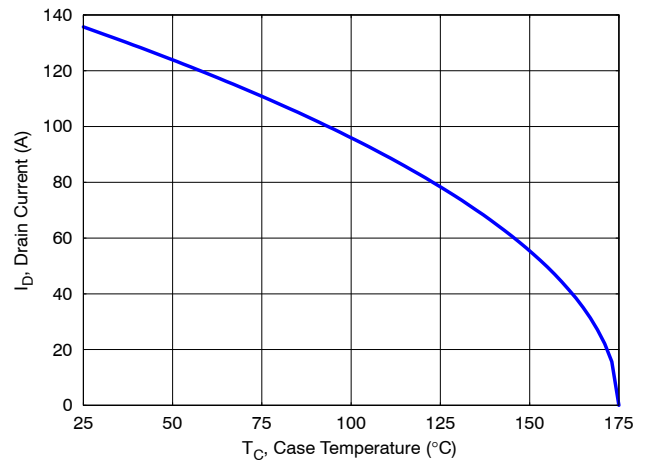


Figure 14. Maximum Current vs. Case Temperature

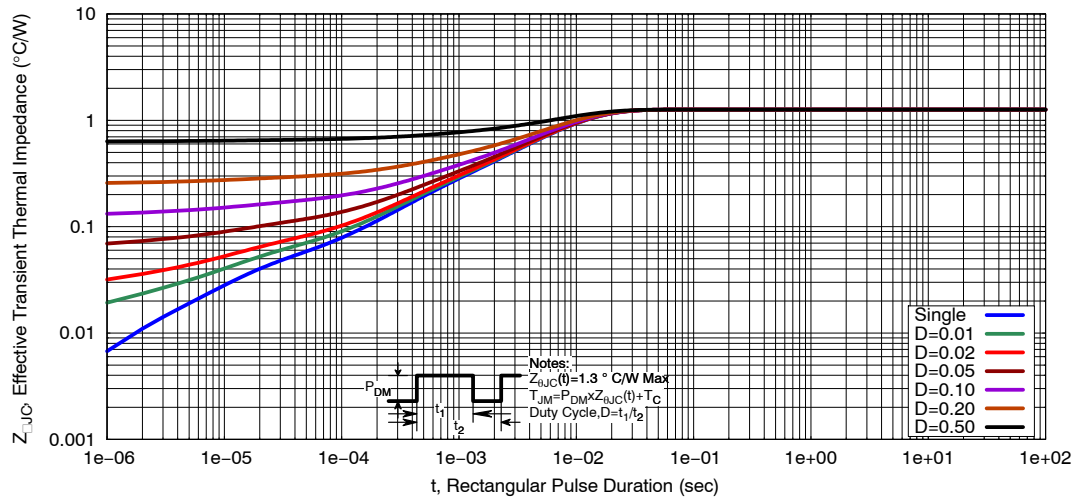


Figure 15. Transient Thermal Response

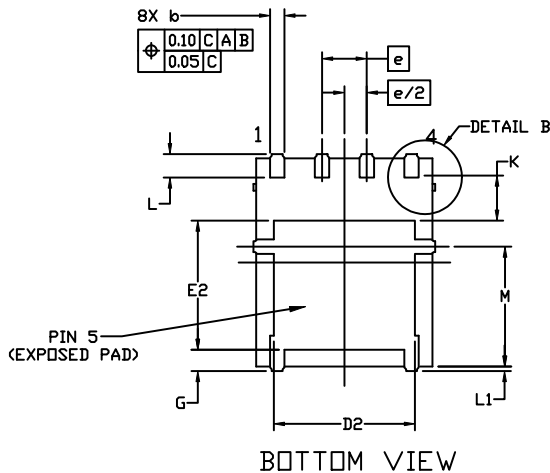
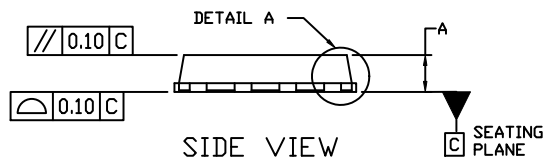
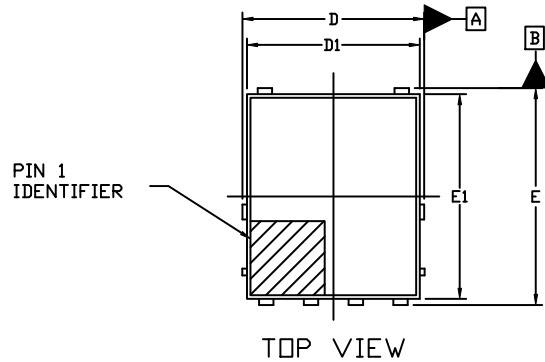
NVMFWS3D0N08X

PACKAGE DIMENSIONS

DFNW5 5x6 (FULL-CUT SO8FL WF)

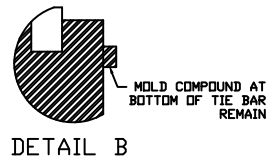
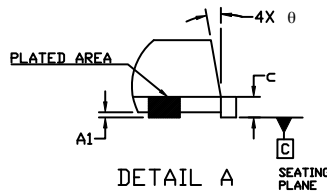
CASE 507BA

ISSUE A

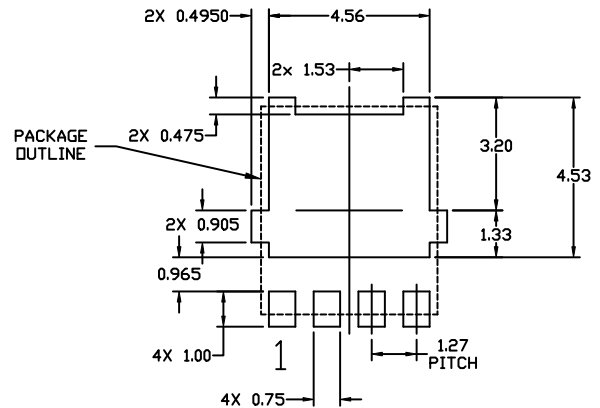


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.



MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.150 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



- * For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NVMFWS3D0N08X

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marketing.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFETs](#) category:

Click to view products by [ON Semiconductor](#) manufacturer:

Other Similar products are found below :

[MCH6422-TL-E](#) [IRFD120](#) [IRFY240C](#) [JANTX2N5237](#) [2SJ277-DL-E](#) [2SK2267\(Q\)](#) [BUK455-60A/B](#) [TK100A10N1,S4X\(S](#) [MIC4420CM-TR](#)
[IRFS350](#) [VN1206L](#) [NDP4060](#) [IPS70R2K0CEAKMA1](#) [AON6932A](#) [2N4352](#) [TS19452CS RL](#) [TK31J60W5,S1VQ\(O](#) [TK16J60W,S1VQ\(O](#)
[2SK2614\(Te16L1,Q\)](#) [JANTX2N6798](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [DMN1053UCP4-7](#) [SCM040600](#) [NTE2384](#) [2N7000TA](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)
[2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [IPB45P03P4L11ATMA2](#) [BXP2N20L](#) [BXP2N65D](#) [BXT330N06D](#) [TSM60NB380CP](#) [ROG](#)
[RQ7L055BGTCTCR](#) [SLF10N65ABV2](#)